WG4 Updates & Discussion

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Marco Mandurrino (marco.mandurrino@cern.ch)

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1 – Feedback from the session(s)



- Very precious contributions about Monte Carlo status and developments
 - LGAD, SiPM, 3D sensor technologies are covered
 - interaction particles/matter module (→GEANT4)
 - signal digitization
 - time-dependent weighting field/potential and space-charge effects
 - integration of new material parameters

WG4 research goals <2027	
	Description
RG 4.1	Flexible CMOS simulation adaptable to different tech- nology nodes and development of connections between tools for device-level simulation and electronic circuit de- sign/validation
RG 4.2	Implementation of newly measured semiconductor proper- ties into TCAD and MC simulations tools
RG 4.3	Definition of benchmark for validating the radiation damage models with measurements and different benchmark models.
RG 4.4	Developing of bulk and surface model for 10^{16} cm ⁻² $< \Phi_{eq} < 10^{17}$ cm ⁻²
RG 4.5	Collate solutions from different MC tools and develop an algorithm to include adaptive electric and weighting fields

1 – Feedback from the session(s)



- Other relevant feedback from this and other sessions
 - radiation damage models: <u>M. Bomben</u>, <u>V. Subert</u> WG3, <u>J. Burin</u> & <u>P. Gaggl</u> WP3 ⇒ RG 4.3, 4.4
 - CMOS sensor simulation: <u>H. Wennlöf</u> ⇒ RG 4.1
 - front-end simulation: <u>L. Tlustos</u> \Rightarrow **RG 4.1**
 - simulations of new materials: <u>J. Burin</u>, <u>S. Xiao</u> ⇒ RG 4.2

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2 – Updates on WG4



- WG4 convener
 - Håkan Wennlöf (DESY) has accepted the role of WG4 convener
- Expressions of Interest
 - we received a new possible expression of interest from Cambridge (Sarah Williams) for a project involving WG4 and WG3 about comparison of TCT measurements of irradiated sensors to TCAD simulation ⇒ RG 4.3 (definition of benchmark for validating the radiation damage models with measurements)
 - the number of participant Institutes rises to 30
- WG4 Structure and Organization
 - Liaison Persons (LP) survey
 - General Meeting time slot survey



3 – WG4 Structure and Organization

DRD3 - wG4 -

- Liaisons Persons (LP). Very few questionnaires have been filled out. The outcome is that few people cover all the groups. Three possible approaches
 - no LP, due to the tight superposition of WG4 with other WGs and WPs
 - LP only for "orthogonal" groups: WG7 (interconnections), WG8, DRD7
 - benefit from the work of LP appointed by the other groups

General Meetings

- 15 questionnaires submitted, so far
- the present consensus is on **Monday**, **3pm 4pm** (CERN time)
- we would wait for more submissions: https://indico.cern.ch/event/1413316/surveys/5458
- then, we will organize the 1st WG4 General Meeting, indicatively in mid/late July (newdle-basis)
- The task, at least at the very beginning, is to have a **complete view** of all the ongoing activities and search for **possible synergies** among sub-groups that **promote the achievement of RG**

4 – Topics for Discussion



- Any other ideas about the Liaisons Persons (LP) appointment?
- Content of the 1st WG4 General Meeting:
 - round-table?
 - focused presentations?
 - discuss "urgent" tasks related to selected projects?
- Are there topics not covered by our WG?
- AoB?

Just to remind you our Useful Links, in case of late comments:

- WG4 webpage: <u>https://drd3.web.cern.ch/wg4</u>
- WG4 e-group: <u>drd3-wg4-simulations</u>
- WG4 contact email: <u>drd3-wg4-conveners@cern.ch</u>
- DRD3 Scientific Proposal (v3.1): pdf



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WG4 Research Goals (2024-2026)



- RG 4.1 Flexible CMOS simulation adaptable to different technology nodes and development of connections between tools for device-level simulation and electronic circuit design/validation
- **RG 4.2** Implementation of **newly measured semiconductor properties** into TCAD and MC simulations tools
- **RG 4.3** Definition of **benchmark** for validating the **radiation damage models** with measurements and different benchmark models
- **RG 4.4** Developing of **bulk and surface model** for 10^{16} cm⁻² < Φ_{eq} < 10^{17} cm⁻²
- RG 4.5 Collate solutions from different MC tools and develop an algorithm to include adaptive electric and weighting fields

WG4 Activities 1/2 (2024-2026)



- TCAD activities will focus on providing verification of tools (mainly Silvaco and Synopsys, but also looking to other tools emerging) implementation of new physics models (impact ionization, mobility parametrization etc.), exporting tools, communication with software companies (e.g. implementation of WGs) and keeping the implementation of common solutions to device simulations.
- TCAD simulations will be complemented with charge transport simulation tools Monte Carlo tools allowing detailed studies of complex sensor performance. Different tools have been developed so far, but currently, the most supported and advanced tools are Allpix Squared and Garfield++, which will form the main/production framework, while other tools will continue to be used as verification and development tools. It is foreseen that improvements in MC simulations will eventually be integrated into AllPix2 and Garfield++. One obstacle for Monte-Carlo tools is currently the lack of implementing adaptive/time-dependent weighting and electric fields in induced current simulations.
- Modeling of the radiation damage in simulations has been evolving over the last two decades, but there is not a general model that, starting from the defect levels, comprehensively describes all the macroscopic properties of silicon, especially at extreme fluences (WG3). This is why it is important to define a common framework for process simulation, aimed at evaluating the impact of such model on innovative devices, technologies or materials.

WG4 Activities 2/2 (2024-2026)



- Development of signal processing tools that can be used with MC and TCAD tools and general digitization models for different sensors technologies.
- Owing to the emerging technology requirements of near future high-energy physics experiments, the
 present WG has to adopt long-term strategies to promote/initiate discussion with designers of future
 experiments, involved in the development of new detector concepts, to create a link between current
 expertise and next requirements.
- Last important item is since the interdisciplinary nature of simulation the establishment of a cooperation framework among the different WGs and WPs, as well as with other synergistic DRD collaborations.